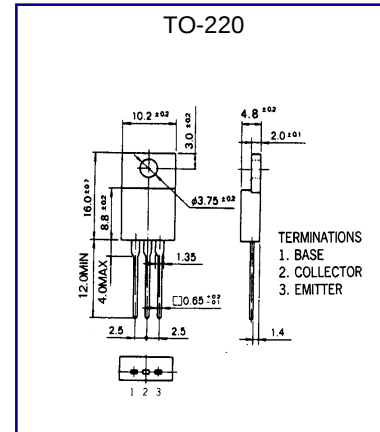


**BU406/406H/408****NPN EPITAXIAL SILICON TRANSISTOR****HIGH VOLTAGE SWITCHING USE IN
HORIZONTAL DEFLECTION OUTPUT STAGE****ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	400	V
Collector-Emitter Voltage	V _{CEO}	200	V
Emitter-Base voltage	V _{EB0}	6	V
Collector Current (DC)	I _C	7	A
Collector Peak Current	I _{CM}	10	A
Base Current (DC)	I _B	4	A
Collector Dissipation (T _c =25°C)	P _C	60	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current (V _{BE} =0)	I _{CES}	V _{CE} = 400V , V _{EB} =0			5	mA
		V _{CE} = 250V , V _{EB} =0			100	μA
					1	mA
Emitter Cutoff Current(I _C =0)	I _{EBO}	V _{CE} = 250V , V _{EB} =0			1	mA
Collector Emitter Saturation Voltage :BU406	V _{CE(sat)}	T _C =150			1	V
:BU408		V _{EB} = 6V , I _C =0			1	V
Base- Emitter Saturation Voltage :BU406	V _{BE(sat)}	I _C =5A, I _B =0.5A			1.2	V
:BU406H		I _C =5A, I _B =0.8A			1.2	V
:BU408		I _C =6A, I _B =1.2A			1.5	V
Current Gain Bandwidth Product	f _T	I _C =5A, I _B =0.5A	10			MHZ
Turn-Off Time :BU406	t _{off}	I _C =5A, I _B =0.8A			0.75	μS
:BU406H		I _C =6A, I _B =1.2A			0.4	μS
:BU408		V _{CE} = 10V , I _C =500mA			0.4	μS
		I _C =5A, I _B =0.5A				
		I _C =5A, I _B =0.8A				
		I _C =6A, I _B =1.2A				